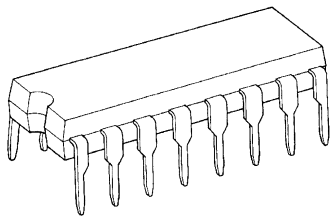
TOSHIBA BIPOLAR DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TD62308BP1G, TD62308BFG

4CH LOW INPUT ACTIVE HIGE−CURRENT DARLINGTON SINK DRIVER

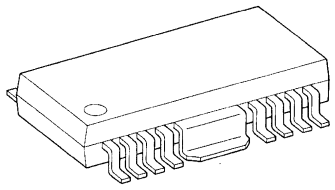
The TD62308BP1G and TD62308BFG are non−inverting transistor array which are comprised of four NPN darlington output stages and PNP input stages.
This device is low level input active driver and are suitable for operation with TTL, 5 V CMOS and 5V Microprocessor which have sink current output drivers.
Applications include relay, hammer, lamp and stepping motor drivers.
This devices are a product for the Pb free(Sn-Ag).

TD62308BP1G



DIP16-P-300-2.54A

TD62308BFG



HSOP16-P-300-1.00

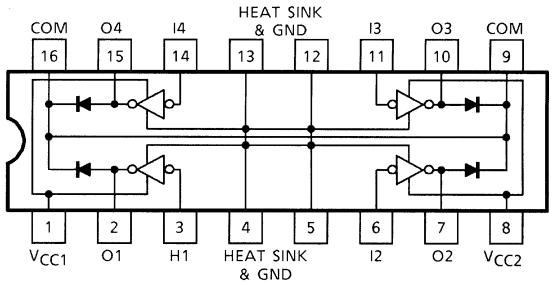
Weight
DIP16−P−300−2.54A : 1.11 g (Typ.)
HSOP16−P−300−1.00 : 0.50 g (Typ.)

FEATURES

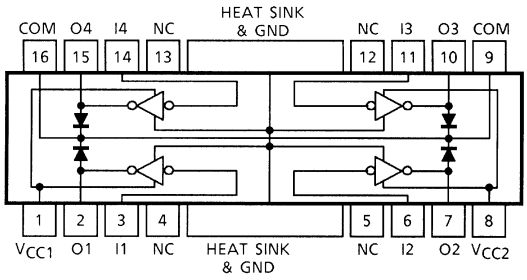
- Two V_{CC} Terminals V_{CC1}, V_{CC2} (Separated)
- Package Type BP1G: DIP−16 pin
  BFG : HSOP−16 pin
- High Sustaining Voltage Output: $V_{CE\ (SUS)}$ = 80 V (Min)
- Output Current (Single Output): I_{OUT} = 1.5 A (Max)
- Output Clamp Diodes
- Low Level Active Input
- GND and SUB Terminal = Heat Sink
- Input Compatible with TTL and 5 V CMOS
- Standard Supply Voltage

PIN CONNECTION (TOP VIEW)

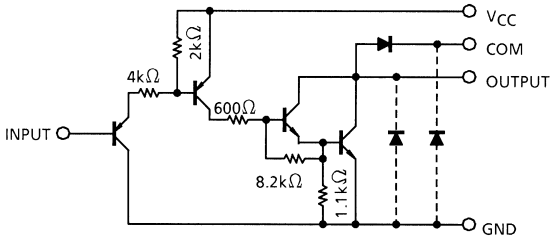
TD62308BP1G



TD62308BFG



SCHEMATICS (EACH DRIVER)



Note : The Output parasitic diodes cannot be used as clamp diodes.

PRECAUTIONS for USING

(1) This IC does not include built-in protection circuits for excess current or overvoltage.
If this IC is subjected to excess current or overvoltage, it may be destroyed.
Hence, the utmost care must be taken when systems which incorporate this IC are designed.
Utmost care is necessary in the design of the output line, VCC, COMMON and GND line since IC may be destroyed due to short−circuit between outputs, air contamination fault, or fault by improper grounding.

(2) If a TD62308BP-1/BF is being used to drive an inductive load (such as a motor, solenoid or relay), Toshiba recommends that the diodes (pins 9 and 16) be connected to the secondary power supply pin so as to absorb the counter electromotive force generated by the load. Please adhere to the device's maximum ratings.
Toshiba recommends that zener diodes be connected between the diodes (pins 9 and 16) and the secondary power supply pin (as the anode) so as to enable rapid absorption of the counter electromotive force. Again, please adhere to the device's maximum ratings.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Supply Voltage		V_{CC}	7	V
Output Sustaining Voltage		$V_{CE\ (SUS)}$	−0.5~80	V
Parasitic Transistor Output Voltage		V_{CEF} (Note 1)	80	V
Output Current		I_{OUT}	1.5	A / ch
Input Current		I_{IN}	−10	mA
Input Voltage		V_{IN}	7	V
Clamp Diode Reverse Voltage		V_R	80	V
Clamp Diode Forward Current		I_F	1.5	A
Power Dissipation	BP1G	P_D	1.47 / 2.7 (Note 2)	W
	BFG		0.9 / 1.4 (Note 3)	
Operating Temperature		T_{opr}	−40~85	°C
Storage Temperature		T_{stg}	−55~150	°C

Note 1: Parasitic Transistor (COMMON - GND - OUTPUT) Output Voltage
Note 2: On Glass Epoxy PCB (50 × 50 × 1.6 mm Cu 50%)
Note 3: On Glass Epoxy PCB (60 × 30 × 1.6 mm Cu 30%)

RECOMMENDED OPERATING CONDITIONS (Ta = −40~85°C)

CHARACTERISTIC		SYMBOL	CONDITION		MIN	TYP.	MAX	UNIT
Supply Voltage		V_{CC}	—		4.5	—	5.0	V
Output Sustaining Voltage		$V_{CE\ (SUS)}$	—		0	—	80	V
Output Current		I_{OUT}	DC 1 Circuit, Ta = 25°C		0	—	1.25	A / ch
	BP1G (Note1)		T_{pw} = 25 ms 4 Circuits T_j = 120°C Ta = 85°C	Duty = 10%	0	—	1.20	
				Duty = 50%	0	—	0.35	
	BP1G (Note2)			Duty = 10%	0	—	0.75	
				Duty = 50%	0	—	0.18	
Input Voltage		V_{IN}	—		0	—	25	V
	Output On	$V_{IN\ (ON)}$	—		0	—	V_{CC} −3.6	V
	Output Off	$V_{IN\ (OFF)}$	—		V_{CC} −1.0	—	V_{CC}	
Clamp Diode Reverse Voltage		V_R	—		—	—	80	V
Clamp Diode Forward Current		I_F	—		—	—	1.25	A
Power Dissipation	BP1G	P_D	Ta = 85°C	(Note 1)	—	—	1.4	W
	BFG		Ta = 85°C	(Note 2)	—	—	0.7	

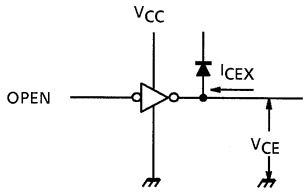
Note 1: On Glass Epoxy PCB (50 × 50 × 1.6 mm Cu 50%)
Note 2: On Glass Epoxy PCB (60 × 30 × 1.6 mm Cu 30%)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

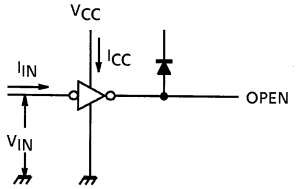
CHARACTERISTIC		SYMBOL	TEST CIR−CUIT	TEST CONDITION	MIN	TYP.	MAX	UNIT
Input Voltage	"H" level	V_{IH}	—	—	V_{CC} −1.6	—	V_{CC}	V
	"L" level	V_{IL}	—	—	—	—	V_{CC} −3.6	
Input Current	"H" level	I_{IH}	2	—	—	—	10	μA
	"L" level	I_{IL}	2	V_{CC} = 5.5 V, V_{IN} = 0.4 V	—	−0.05	−0.36	mA
Output Leakage Current		I_{CEX}	1	V_{OUT} = 80 V, Ta = 25°C	—	—	50	μA
				V_{OUT} = 80 V, Ta = 85°C	—	—	100	
Output Saturation Voltage		$V_{CE\ (sat)}$	3	V_{CC} = 4.5 V, I_{OUT} = 1.25 A	—	1.3	1.8	V
Clamp Diode Reverse Current		I_R	4	V_R = 80 V, Ta = 25°C	—	—	50	μA
Clamp Diode Forward Voltage		V_F	5	I_F = 1.25 A	—	1.5	2.0	V
Supply Current	Output On	$I_{CC\ (ON)}$	2	V_{CC} = 5.5 V, V_{IN} = 0 V	—	8.5	12.5	mA / ch
	Output Off	$I_{CC\ (OFF)}$	2	V_{CC} = 5.5 V, V_{IN} = V_{CC}	—	—	10	μA
Turn−On Delay		t_{ON}	6	V_{OUT} = 80 V, RL = 68 Ω	—	0.2	—	μs
Turn−Off Delay		t_{OFF}			—	5.0	—	
Parasitic Transistor Output Voltage		V_{CEF}	7	I_{CEF} = 150 mA	80	—	—	V

TEST CIRCUIT

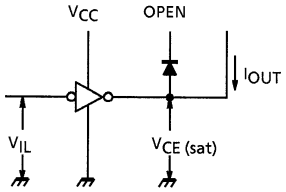
1. I_{CEX}



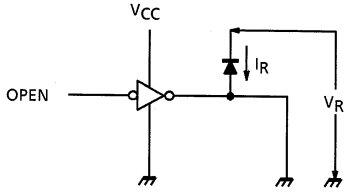
2. I_{CC}, I_{IN}



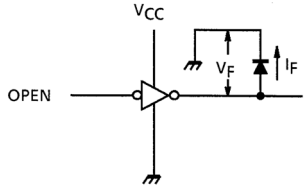
3. $V_{CE\ (sat)}$



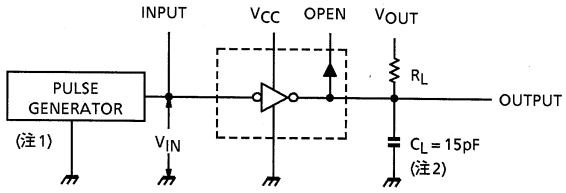
4. I_R

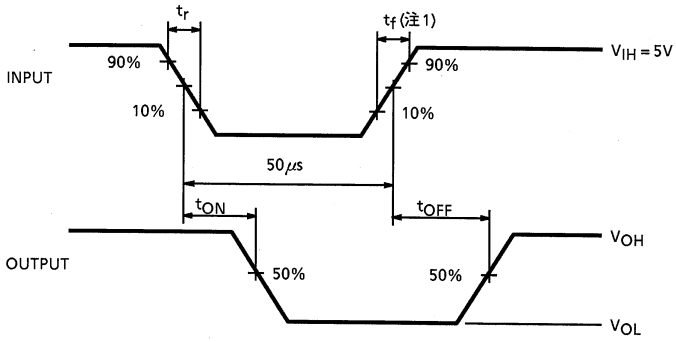


5. V_F



6. t_{ON}, t_{OFF}

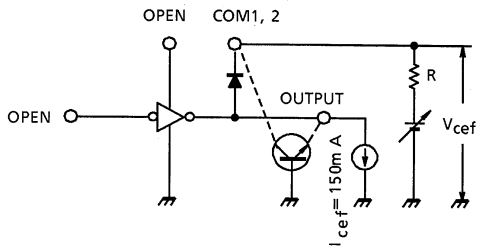




Note 1: Pulse width 50 μs, Duty Cycle 10%
Output Impedance 50 Ω tr ≤ 5 ns, tf ≤ 10 ns

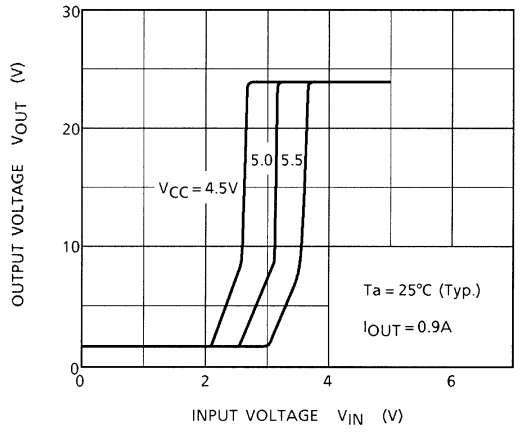
Note 2: C_L includes probe and jig capacitance.

7. V_{cef}

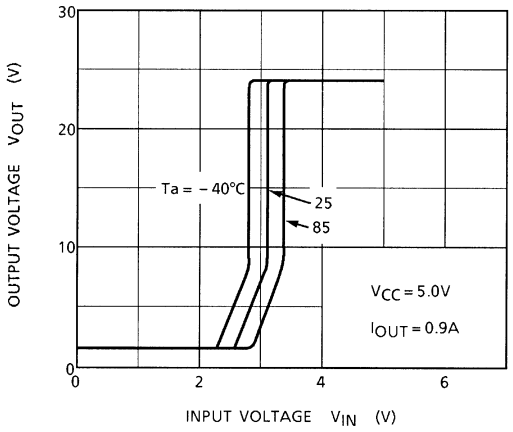


I_{cef} = 150mA
(at Single Pulse = 5ms)

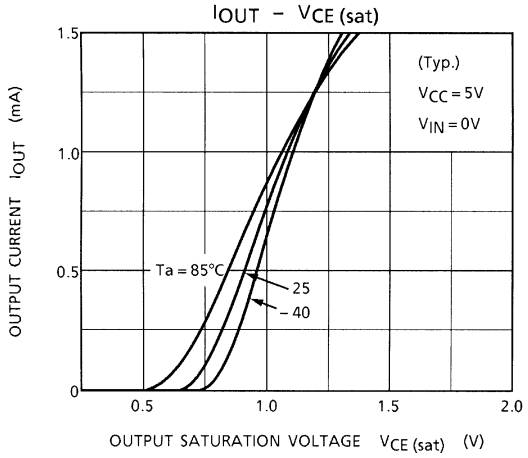
V_{OUT} – V_{IN}



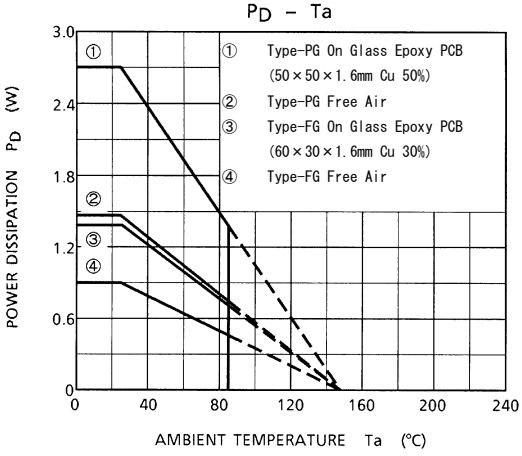
V_{OUT} – V_{IN}



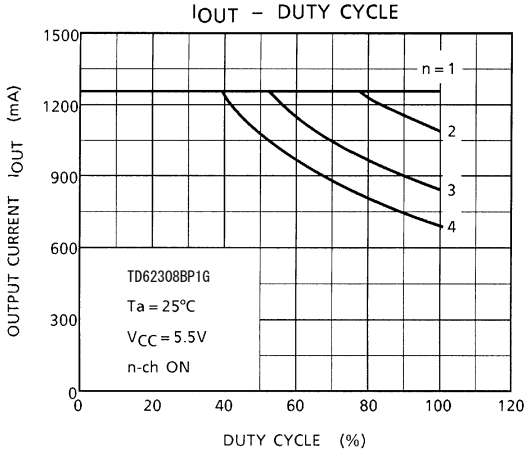
I_{OUT} – $V_{CE\ (sat)}$



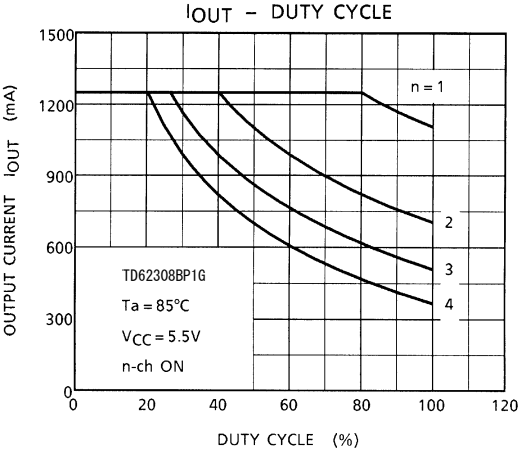
P_D – Ta

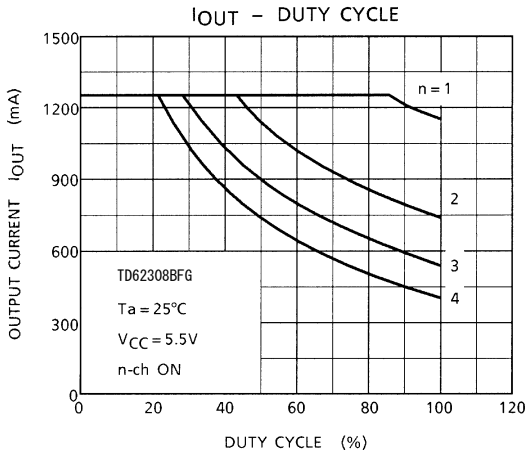


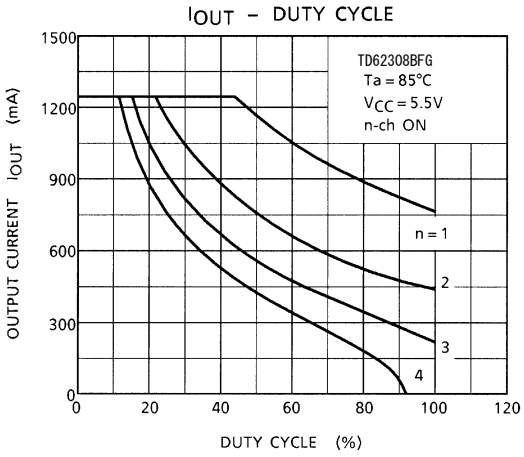
I_{OUT} – DUTY CYCLE



I_{OUT} – DUTY CYCLE

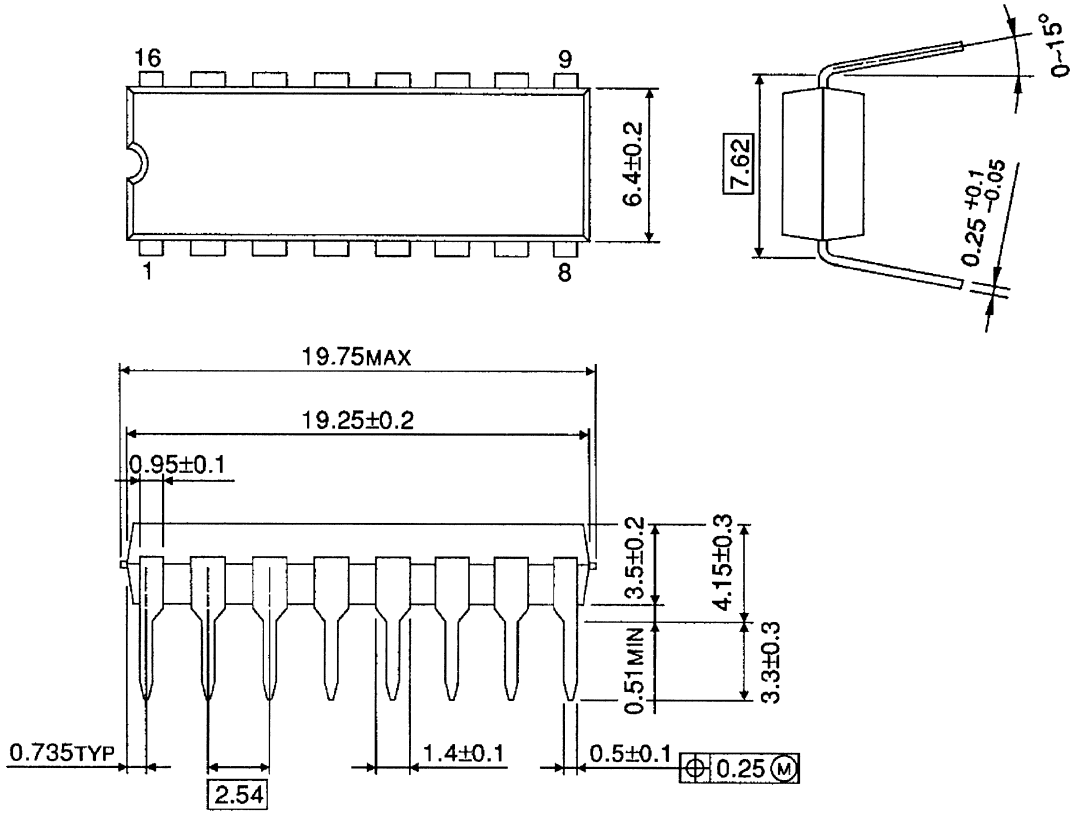



IOUT – DUTY CYCLE
OUTPUT CURRENT IOUT (mA)
1500
1200
900
600
300
0
0
20
40
60
80
100
120
DUTY CYCLE (%)
n = 1
2
3
4
TD62308BFG
Ta = 25°C
VCC = 5.5V
n-ch ON


IOUT – DUTY CYCLE
OUTPUT CURRENT IOUT (mA)
1500
1200
900
600
300
0
0
20
40
60
80
100
120
DUTY CYCLE (%)
TD62308BFG
Ta = 85°C
VCC = 5.5V
n-ch ON
n = 1
2
3
4

PACKAGE DIMENSIONS

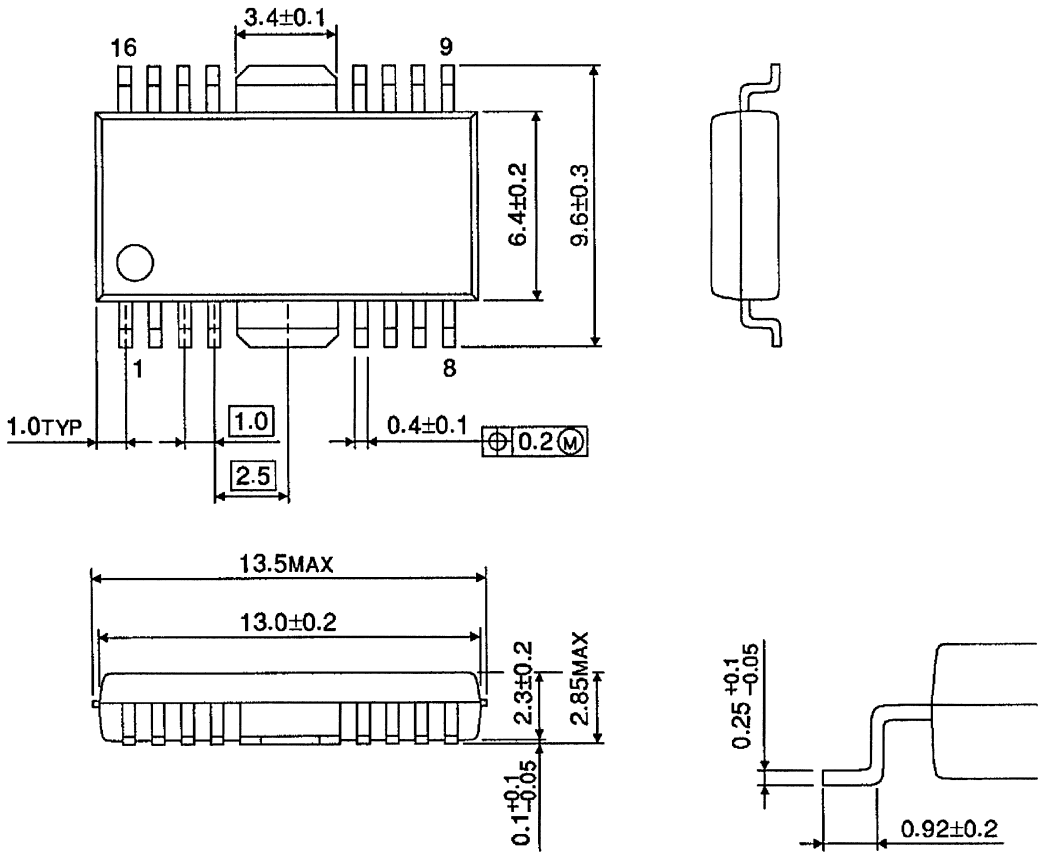
DIP16-P-300-2.54A Unit: mm



Weight: 1.11 g (Typ.)

PACKAGE DIMENSIONS

HSOP16-P-300-1.00 Unit: mm



Weight: 0.50 g (Typ.)

About solderability, following conditions were confirmed

- Solderability

  (1) Use of Sn-63Pb solder Bath
  - solder bath temperature = 230°C
  - dipping time = 5 seconds
  - the number of times = once
  - use of R-type flux

  (2) Use of Sn-3.0Ag-0.5Cu solder Bath
  - solder bath temperature = 245°C
  - dipping time = 5 seconds
  - the number of times = once
  - use of R-type flux

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030619EBA

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